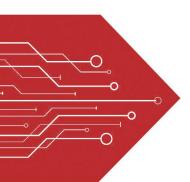
MSKSEMI















ESD

TVS

TSS

MOV

GDT

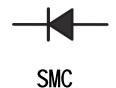
PLED

Broduct data sheet



VOLTAGE RANGE 50 to 1000 Volts CURRENT 5.0 Ampere





FEATURES

- * Ideal for surface mount applications
- * Easy pick and place
- * Built-in strain relief
- * Fast switching speed

MECHANICAL DATA

- * Case: Molded plastic
- * Epoxy: UL 94V-0 rate flame retardant
- * Metallurgically bonded construction
- * Polarity: Color band denotes cathode end
- * Mounting position: Any
- * Weight: 0.21 grams

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating 25°C ambient temperature unless otherwies specified. Single phase half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

TYPE NUMBER	US5A	US5B	US5D	US5E	US5G	US5J	US5K	US5M	UNITS
Maximum Recurrent Peak Reverse Voltage		100	200	300	400	600	800	1000	V
Maximum RMS Voltage		70	140	210	280	420	560	700	V
Maximum DC Blocking Voltage		100	200	300	400	600	800	1000	V
Maximum Average Forward Rectified Current									
at Ta=55°C	a=55°C 5.0			Α					
Peak Forward Surge Current, 8.3 ms single half sine-wave									
superimposed on rated load (JEDEC method)		120					Α		
Maximum Instantaneous Forward Voltage at 5.0A		1.0 1.3 1.7			1.7		V		
Maximum DC Reverse Current Ta=25°C	everse Current Ta=25°C 10		μА						
at Rated DC Blocking Voltage Ta=100°C	200		μА						
Maximum Reverse Recovery Time (Note 1)		50 75				nS			
Typical Junction Capacitance (Note 2)	15		pF						
Operating and Storage Temperature Range TJ, Tstg		-65—+150					°C		

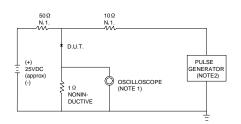
NOTES:

- 1. Reverse Recovery Time test condition: IF=0.5A, IR=1.0A, IRR=0.25A
- 2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.



RATING AND CHARACTERISTIC CURVES (US5A THRU US5M)

FIG.1 -- TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTIC



NOTES:1.RISE TIME = 7ns MAX.INPUT IMPEDANCE = $1M_{\Omega}.22pF$. 2.RISE TIME =10ns MAX.SOURCE IMPEDANCE=50 $\,\Omega.$

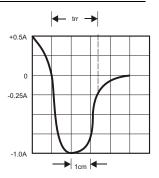
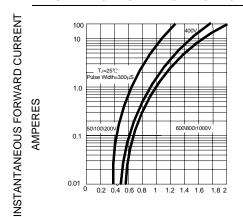
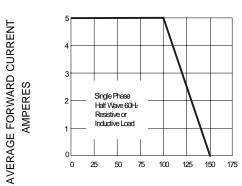


FIG.2 - TYPICAL FORWARD CHARACTERISTIC



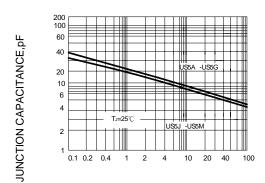
INSTANTANEOUS FORWARD VOLTAGE, VOLTS

FIG.3 -- FORWARD DERATING CURVE



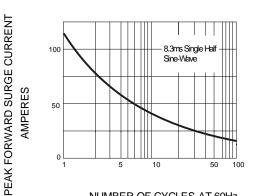
LEAD TEMPERATURE,℃

FIG.4 -- TYPICAL JUNCTION CAPACITANCE



REVERSE VOLTAGE, VOLTS

FIG.5 -- PEAK FORWARD SURGE CURRENT

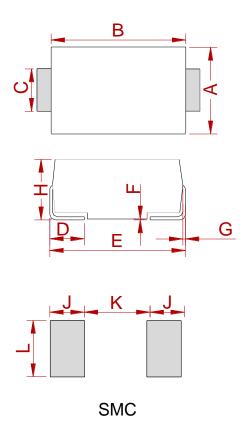


NUMBER OF CYCLES AT 60Hz



Semiconductor Compiance

PACKAGE MECHANICAL DATA



	Dimensions					
Ref.	Millimeters		Inches			
	Min.	Max.	Min.	Max.		
Α	5.75	6.25	0.226	0.246		
В	6.90	7.40	0.272	0.291		
С	2.75	3.25	0.108	0.128		
D	0.95	1.52	0.037	0.060		
E	7.70	8.20	0.303	0.323		
F	0.051	0.203	0.002	0.008		
G	0.15	0.31	0.006	0.012		
Н	2.15	2.62	0.085	0.103		
J	2.40		0.094			
K		4.20		0.165		
L	3.30		0.130			

REEL SPECIFICATION

P/N	PKG	QTY
US5A THRU US5M	SMC	3000



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